



Phase Control Thyristor

Supersedes June 1997 version, DS4648 - 5.2

DS4648 - 5.3 March 1998

APPLICATIONS

- High Power Drives.
- High Voltage Power Supplies.
- DC Motor Control.

KEY PARAMETERS

 $\begin{array}{lll} {\rm V_{DRM}} & 5200{\rm V} \\ {\rm I_{T(AV)}} & 3000{\rm A} \\ {\rm I_{TSM}} & 50000{\rm A} \\ {\rm dVdt^*} & 1000{\rm V/\mu s} \\ {\rm dI/dt} & 300{\rm A/\mu s} \\ \end{array}$

*Higher dV/dt selections available

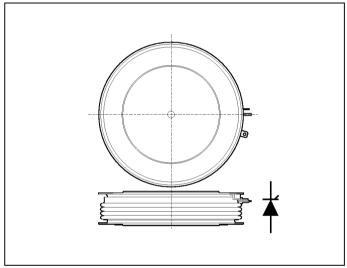
FEATURES

- Double Side Cooling.
- High Surge Capability.
- High Mean Current.
- Fatigue Free.

VOLTAGE RATINGS

Type Number	Repetitive Peak Voltages V _{DRM} V _{RRM} V	Conditions
DCR1675SZ52	5200	$T_{v_i} = 0^{\circ} \text{ to } 125^{\circ}\text{C},$
DCR1675SZ51	5100	$I_{DRM} = I_{RRM} = 500 \text{mA},$
DCR1675SZ50	5000	V_{DRM} , V_{RRM} $t_p = 10 ms$,
DCR1675SZ49	4900	V _{DSM} & V _{RSM} =
DCR1675SZ48	4800	V _{DRM} & V _{RRM} + 100V
		Respectively

Lower voltage grades available.



Outline type code: Z. See package outline for further information.

CURRENT RATINGS

Symbol	Parameter	Conditions	Max.	Units		
Double Side Cooled						
I _{T(AV)}	Mean on-state current	Half wave resistive load, T _{case} = 80°C	3000	Α		
I _{T(RMS)}	RMS value	T _{case} = 80°C	4710	Α		
I _T	Continuous (direct) on-state current	T _{case} = 80°C	4200	Α		
Single Side Cooled (Anode side)						
I _{T(AV)}	Mean on-state current	Half wave resistive load, T _{case} = 80°C	1920	Α		
I _{T(RMS)}	RMS value	$T_{case} = 80^{\circ}C$	3015	Α		
I _T	Continuous (direct) on-state current	$T_{case} = 80^{\circ}C$	2500	Α		

DCR1675SZ

SURGE RATINGS

Symbol	Parameter	Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine; T _{case} = 125°C	40.0	kA
l²t	I ² t for fusing	$V_{R} = 50\% V_{RRM} - 1/4 \text{ sine}$	8.0 x 10 ⁶	A²s
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine; T _{case} = 125°C	50.0	kA
l²t	I ² t for fusing	V _R = 0	12.5 x 10 ⁶	A²s

THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions		Min.	Max.	Units
$R_{th(j-c)}$	Thermal resistance - junction to case	Double side cooled	dc	-	0.0065	°C/W
		Single side cooled	Anode dc	-	0.013	°C/W
			Cathode dc	-	0.013	°C/W
D	Thermal resistance - case to heatsink	Clamping force 83.0kN with mounting compound	Double side	-	0.001	°C/W
R _{th(c-h)}			Single side	-	0.002	°C/W
T _{vj}	Virtual junction temperature	On-state (conducting)		-	135	°C
		Reverse (blocking)		-	125	°C
T _{stg}	Storage temperature range			-55	125	°C
-	Clamping force			74.0	91.0	kN

DYNAMIC CHARACTERISTICS

Symbol	Parameter	Conditions		Тур.	Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C		-	500	mA
dV/dt	Maximum linear rate of rise of off-state voltage	To 67% V_{DRM} T_j = 125°C, gate open circuit.		-	1000	V/μs
dl/dt		e of on-state current Gate source 30V, 10Ω	Repetitive 50Hz	-	150	A/μs
di/di	Hate of rise of off-state current		Non-repetitive	ı	300	A/μs
V _{T(TO)}	Threshold voltage	At T _{vj} = 125°C		ı	1.0	V
r _T	On-state slope resistance	At T _{vj} = 125°C		-	0.15	mΩ
t _{gd}	Delay time	$V_D = 67\%$ V_{DRM} , Gate source 20V, 10Ω $t_r = 0.5 \mu s$, $T_j = 25$ °C		-	1.1	μs
IL	Latching current	$T_j = 25$ °C, $V_D = 5V$			650	mA
I _H	Holding current	$T_j = 25$ °C, $R_{g-k} = \infty$		-	200	mA

GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Conditions		Units
V _{GT}	Gate trigger voltage	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	3.5	V
I _{GT}	Gate trigger current	$V_{DRM} = 5V$, $T_{case} = 25^{\circ}C$	500	mA
V _{GD}	Gate non-trigger voltage	At V _{DRM} T _{case} = 125°C	0.25	V
V _{FGM}	Peak forward gate voltage	Anode positive with respect to cathode	30	٧
V _{FGN}	Peak forward gate voltage	Anode negative with respect to cathode	0.25	V
V _{RGM}	Peak reverse gate voltage		5	٧
I _{FGM}	Peak forward gate current	Anode positive with respect to cathode	30	Α
P _{GM}	Peak gate power	See table, fig.4	150	w
P _{G(AV)}	Mean gate power		10	w

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CURVES

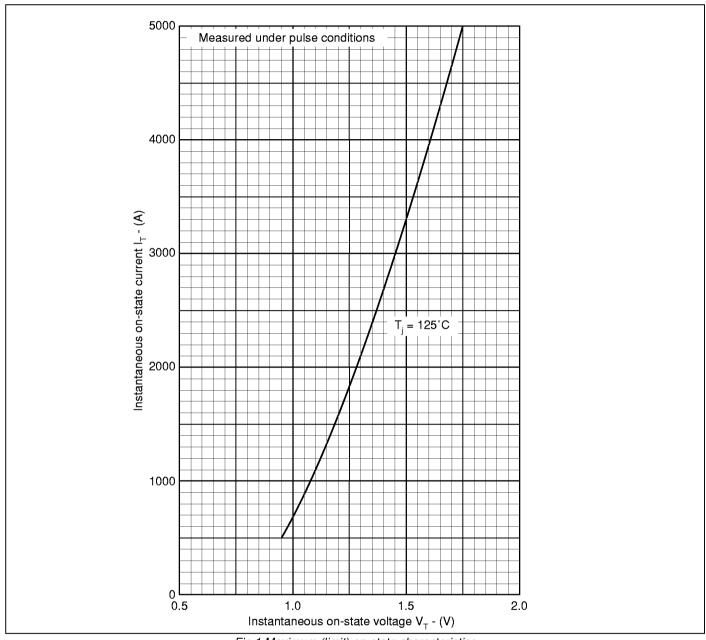


Fig.1 Maximum (limit) on-state characteristics

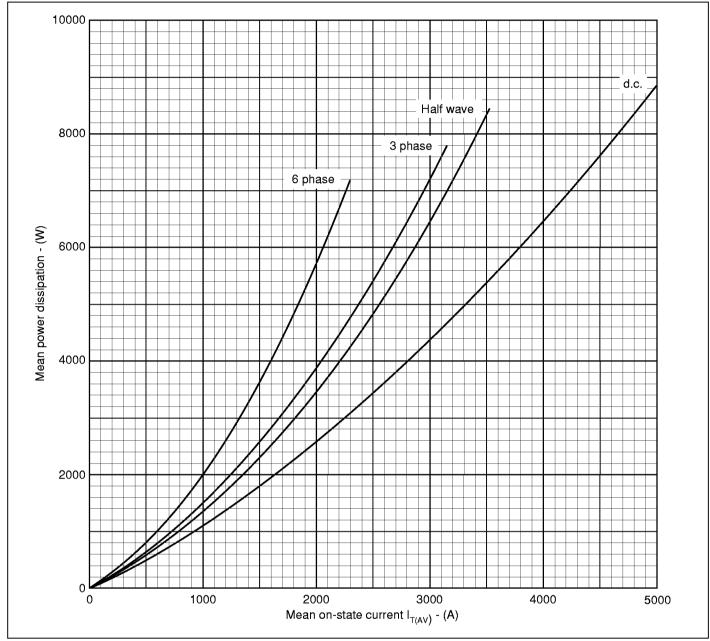


Fig.2 Dissipation curves

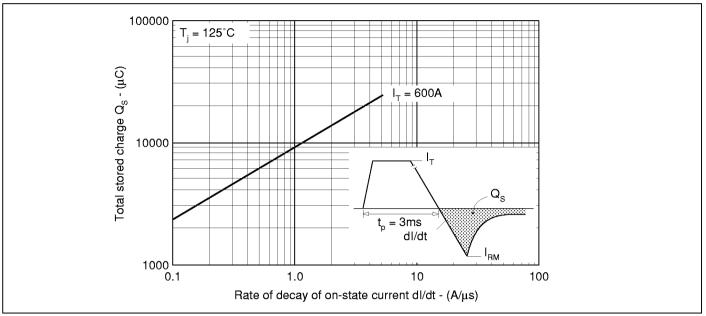


Fig.3 Stored charge

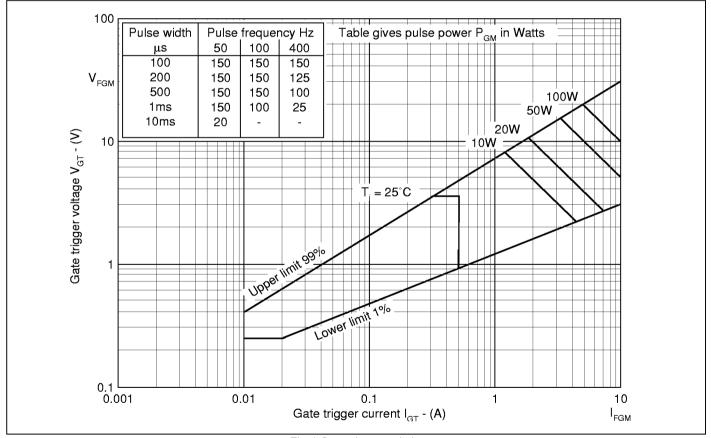


Fig.4 Gate characteristics

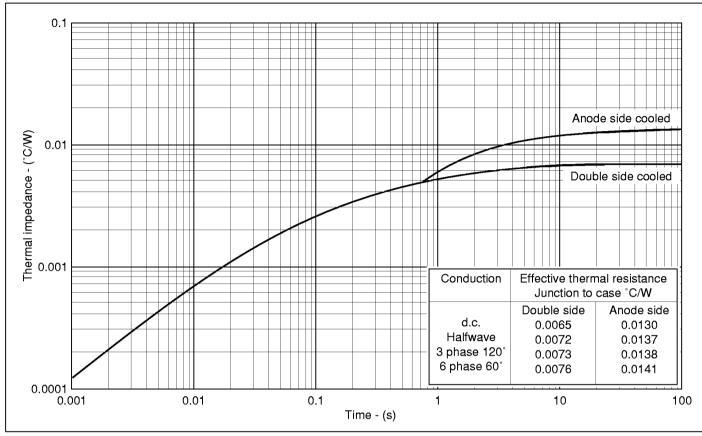


Fig.5 Maximum (limit) transient thermal impedance - junction to case

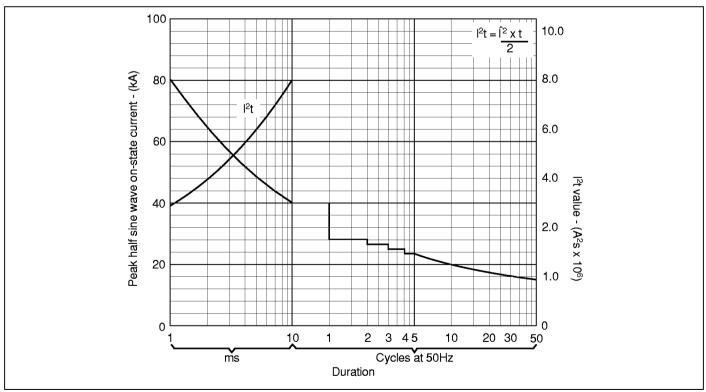
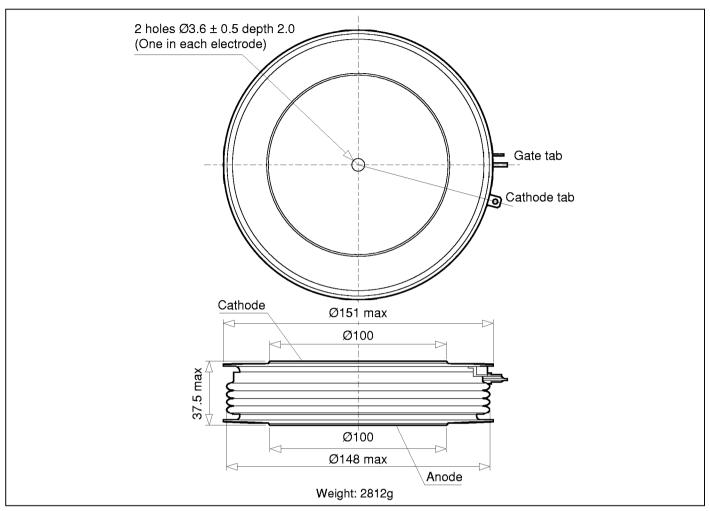


Fig.6 Surge (non-repetitive) on-state current vs time (with 50% V_{RRM} at T_{case}125°C)

DCR1675SZ

PACKAGE OUTLINE - Z

For further package information, please contact your local Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.





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